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LP-MOCVD PROCESS FOR FERROELECTRIC THIN FLLMS WITH PRECISE COMPOSITION CONTROL, H.G. Kim., Dept. Cer. Sci. & Eng. KAIST. 373-Kusong-dong, Yusung-gu, Taejon 305-701 Korea

PZT thin films were prepared by the MOCVD method. Bis(dipivaloyl)methanato lead, zirconium tetra-*t*-butoxide and titanium tetra-*i*-propoxide and oxygen were used as source material. Polycrystallized films with the Well developed. precise composition control perovskite phase were formed on Si(100) substrate. The deposition mechanism of PZT thin film as a function of deposition condition has been investigated, and the structural, compositional and electrical properties of PZT thin films have been examined.

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